Express Mail No. EV060042762US
Atty. Dkt. No. 037267-0135

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant: Takaaki NAGAI et al.

Title: EEPROM SEMICONDUCTOR DEVICE AND METHOD OF FABRICATING THE SAME

Appl. No.: 09/606,159

Filing Date: 06/29/2000

Examiner: P. Brock, II

Art Unit: 2815

CERTIFICATE OF EXPRESS MAILING

I hereby certify that this correspondence is being deposited with the United States Postal Service's "Express Mail Post Office To Addressee" service under 37 C.F.R. § 1.10 on the date indicated below and is addressed to: Commissioner for Patents, Washington, D.C. 20231.

EV060042762US (Express Mail Label Number) December 4, 2002 (Date of Deposit)

Beatriz Valencia (Printed Name)

Beatriz Valencia (Signature)

AMENDMENT TRANSMITTAL

Commissioner for Patents
Washington, D.C. 20231

Sir:

Transmitted herewith is an amendment in the above-identified application.

[ ] Small Entity status under 37 C.F.R. § 1.9 and § 1.27 has been established by a Small Entity statement previously submitted.

[ ] Small Entity statement is enclosed.

[**X**] The fee required for additional claims is calculated below:

	Claims as Amended		Previously Paid For		Extra Claims Present		Rate		Additional Claims Fee
Total Claims:	6	–	20	=	0	x	$18.00	=	$0.00
Independents:	2	–	3	=	0	x	$84.00	=	$0.00
First presentation of any Multiple Dependent Claims:						+	$280.00	=	$0.00
							CLAIMS FEE TOTAL:	=	$0.00

[**X**] Applicant hereby petitions for an extension of time under 37 C.F.R. §1.136(a) for the total number of months checked below:

[ ]	Extension for response filed within the first month:	$110.00	$0.00
[ ]	Extension for respons filed within the second month:	$400.00	$0.00
[X]	Extension for response filed within the third month:	$920.00	$920.00
[ ]	Extension for response filed within the fourth month:	$1,440.00	$0.00
[ ]	Extension for response filed within the fifth month:	$1,960.00	$0.00
		EXTENSION FEE TOTAL:	$920.00
		CLAIMS AND EXTENSION FEE TOTAL:	$920.00
[ ]		Small Entity Fees Apply (subtract ½ of above):	$0.00
		TOTAL FEE:	$920.00

[ ] Please charge Deposit Account No. 19-0741 in the amount of $920.00. A duplicate copy of this transmittal is enclosed.

[**X**] A check in the amount of $920.00 is enclosed.

[**X**] The Commissioner is hereby authorized to charge any additional fees which may be required regarding this application under 37 C.F.R. §§ 1.16-1.17, or credit any overpayment, to Deposit Account No. 19-0741. Should no proper payment be enclosed herewith, as by a check being in the wrong amount, unsigned, post-dated, otherwise improper or informal or even entirely missing, the Commissioner is authorized to charge the unpaid amount to Deposit Account No. 19-0741.

Please direct all correspondence to the undersigned attorney or agent at the address indicated below.

Respectfully submitted,

Date 12-4-02

By _____

FOLEY & LARDNER
Customer Number: 22428
22428
PATENT TRADEMARK OFFICE
Telephone: (310) 975-7895
Facsimile: (202) 672-5399

Richard D. Malone
Attorney for Applicant
Registration No. 51,991

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

#8/0
Amdt
J.McMillan
1/7/03

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AMENDMENT AND REQUEST FOR

RECONSIDERATION UNDER 37 C.F.R. § 1.111

Commissioner for Patents
Washington, D.C. 20231

Sir:

In response to the Office Action mailed June 5, 2001, time for response to which is extended three months (to December 5, 2002) by the accompanying petition, please amend the above-identified application as follows:

IN THE CLAIMS:

Please enter the following amended claims:

amdt
D1

21. (Amended) A method of fabricating an EEPROM semiconductor device having a plurality of memory cell transistors, comprising the steps of:

(a) forming a plurality of field insulating films in parallel with one another on a semiconductor substrate;

(b) forming a first gate insulating film in each of active regions;

(c) forming a plurality of first polysilicon strips in parallel with one another;

(d) forming a second gate insulating film and a second polysilicon layer all over the product resulting from said step (c);